

### **1. General description**

Planar passivated sensitive gate four quadrant triac in a SOT82 (SIP3) plastic package intended for use in general purpose bidirectional switching and phase control applications. This "series E" sensitive gate triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 2. Features and benefits

- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants
- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- · Low holding current for low current loads and lowest EMI at commutation
- Compact package

### 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control

### 4. Quick reference data

| Symbol              | Parameter                                | Conditions   | Values |     |     |     | Unit |
|---------------------|--|--|--------|-----|-----|-----|------|
| Absolute            | maximum rating                           |  |        |     |     |     |      |
| V <sub>drm</sub>    | repetitive peak off-state voltage        |  | 600    |     |     |     | V    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; T <sub>mb</sub> ≤ 107 °C; <u>Fig. 1;</u><br><u>Fig. 2; Fig. 3</u>                      | 4      |     |     |     | A    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; T <sub>j(init)</sub> = 25 °C;<br>t <sub>p</sub> = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u> | 25     |     |     | A   |      |
| Symbol              | Parameter                                | Conditions   |        | Min | Тур | Max | Unit |
| Static ch           | aracteristics                            |  |        |     |     |     |      |
| I <sub>GT</sub>     | gate trigger current                     | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>        |        | -   | 2.5 | 10  | mA   |
|                     |  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>        |        | -   | 4   | 10  | mA   |
|                     |  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>        |        | -   | 5   | 10  | mA   |
|                     |  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>        |        | -   | 11  | 25  | mA   |
| I <sub>H</sub>      | holding current                          | V <sub>D</sub> = 12 V; T <sub>i</sub> = 25 °C; <u>Fig. 9</u>   |        | -   | 2.2 | 15  | mA   |

# **5. Pinning information**

| Table 2. | <b>Pinning info</b> | rmation                        |                    |                |
|----------|---------------------|--------------------------------|--------------------|----------------|
| Pin      | Symbol              | Description                    | Simplified outline | Graphic symbol |
| 1        | T1                  | main terminal 1                | ()                 |                |
| 2        | T2                  | main terminal 2                |                    | N              |
| 3        | G                   | gate                           |                    |                |
| mb       | T2                  | mounting base; main terminal 2 | ~r                 | G<br>sym051    |
|          |                     |                                |                    |                |
|          |                     |                                |                    |                |
|          |                     |                                |                    |                |
|          |                     |                                |                    |                |

# 6. Ordering information

| Table 3. Ordering information |                 |                       |                |                           |                 |                       |  |  |  |  |
|-------------------------------|-----------------|-----------------------|----------------|---------------------------|-----------------|-----------------------|--|--|--|--|
| Type number                   | Package<br>Name | Orderable part number | Packing method | Small packing<br>quantity | Package version | Package<br>issue date |  |  |  |  |
| BT134-600E                    | SOT82           | BT134-600E,127        | Tube           | 50                        | SOT82           | 11-Jun-1997           |  |  |  |  |

## 7. Marking

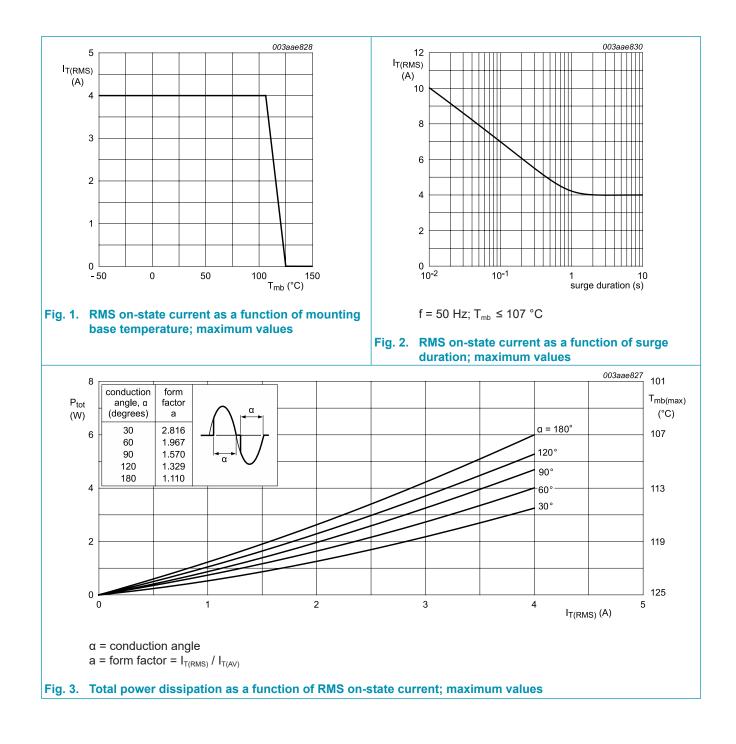
| Table 4. Marking codes |               |
|------------------------|---------------|
| Type number            | Marking codes |
| BT134-600E             | 600E<br>BT134 |

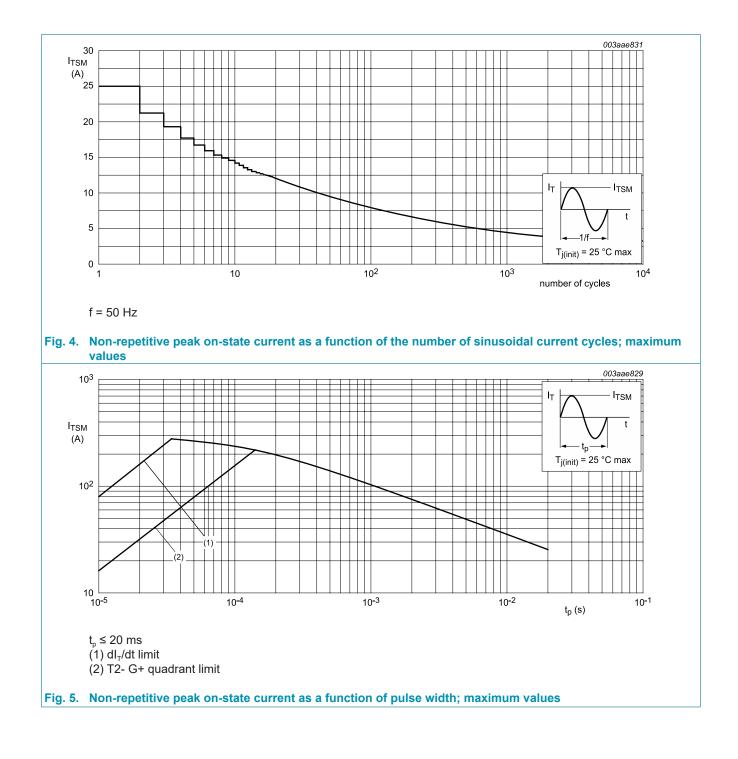
# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

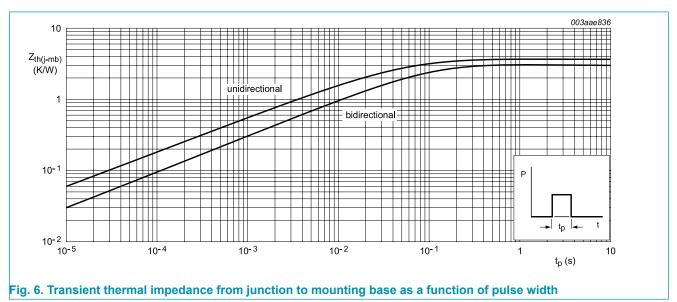
| Symbol              | Parameter                                | Conditions  | Values     | Unit             |
|---------------------|--|---|------------|------------------|
| $V_{\text{DRM}}$    | repetitive peak off-state voltage        |   | 600        | V                |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; $T_{mb} \le 107$ °C; <u>Fig 1</u> ; <u>Fig 2</u> ; <u>Fig 3</u>         | 4          | А                |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ;<br>Fig 4; Fig 5 | 25         | A                |
|                     |  | full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms                                  | 27         | A                |
| l <sup>2</sup> t    | I <sup>2</sup> t for fusing              | t <sub>P</sub> = 10 ms; SIN   | 3.1        | A <sup>2</sup> s |
| dl <sub>⊤</sub> /dt | rate of rise of on-state                 | I <sub>G</sub> = 20 mA; T2+ G+  | 50         | A/µs             |
|                     | current                                  | I <sub>G</sub> = 20 mA; T2+ G-  | 50         | A/µs             |
|                     |  | I <sub>G</sub> = 20 mA; T2- G-  | 50         | A/µs             |
|                     |  | I <sub>G</sub> = 50 mA; T2- G+  | 10         | A/µs             |
| I <sub>GM</sub>     | peak gate current                        |   | 2          | А                |
| P <sub>GM</sub>     | peak gate power                          |   | 5          | W                |
| P <sub>G(AV)</sub>  | average gate power                       | over any 20 ms period   | 0.5        | W                |
| T <sub>stg</sub>    | storage temperature                      |   | -40 to 150 | °C               |
| Tj                  | junction temperature                     |   | 125        | °C               |





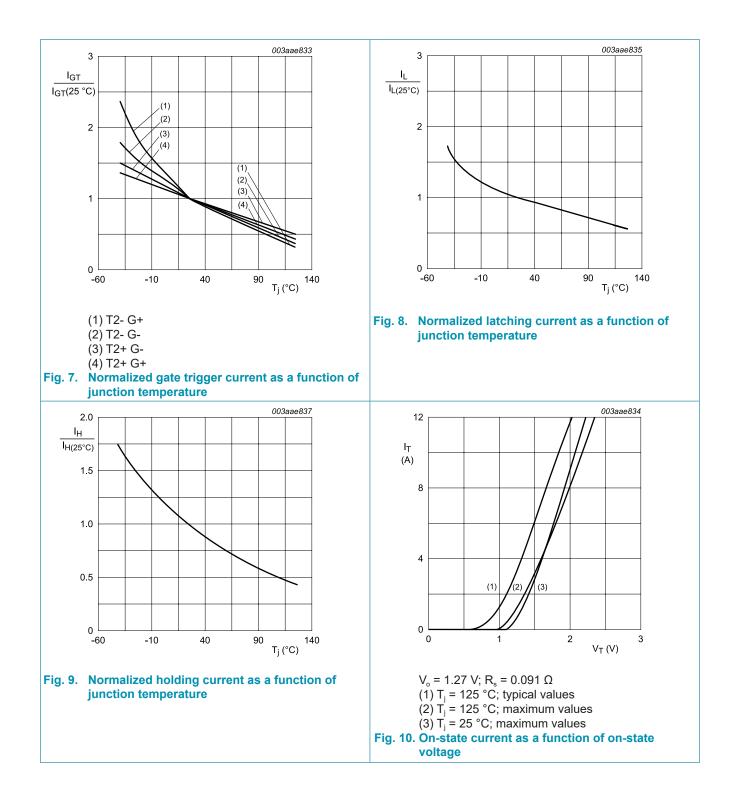
## 9. Thermal characteristics

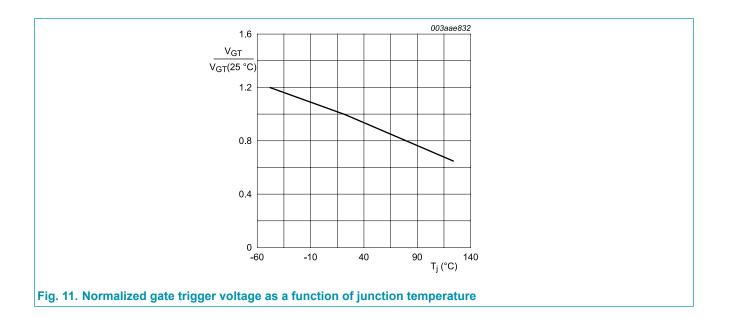
| Symbol  | Parameter   | Conditions               | Min | Тур | Max | Unit |
|---|---|--------------------------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> thermal resistance<br>from junction to<br>mounting base |   | half cycle; <u>Fig 6</u> | -   | -   | 3.7 | K/W  |
|   |   | full cycle; <u>Fig 6</u> | -   | -   | 3   | K/W  |
| $R_{\text{th(j-a)}}$  | thermal resistance<br>from junction to<br>ambient | in free air              | -   | 100 | -   | K/W  |



## **10. Characteristics**

| Symbol              | Parameter                         | Conditions   | Min  | Тур | Max | Unit |
|---------------------|-----------------------------------|--|------|-----|-----|------|
| Static cha          | aracteristics                     |  |      |     |     | _    |
| I <sub>GT</sub>     | gate trigger current              | $V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2+ G+};$<br>T <sub>j</sub> = 25 °C; Fig. 7                               | -    | 2.5 | 10  | mA   |
|                     |                                   | $V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2+ G-};$<br>T <sub>j</sub> = 25 °C; Fig. 7                               | -    | 4   | 10  | mA   |
|                     |                                   | $V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2- G-};$<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                        | -    | 5   | 10  | mA   |
|                     |                                   | $V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2- G+};$<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                        | -    | 11  | 25  | mA   |
| IL I                | latching current                  | $V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G+};$<br>T <sub>j</sub> = 25 °C; <u>Fig. 8</u>                            | -    | 3   | 15  | mA   |
|                     |                                   | $V_{D}$ = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-;<br>T <sub>j</sub> = 25 °C; <u>Fig. 8</u>   | -    | 10  | 20  | mA   |
|                     |                                   | V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-;<br>T <sub>j</sub> = 25 °C; <u>Fig. 8</u>  | -    | 2.5 | 15  | mA   |
|                     |                                   | $V_{D}$ = 12 V; I <sub>G</sub> = 0.1 A; T2- G+;<br>T <sub>j</sub> = 25 °C; Fig. 8  | -    | 4   | 20  | mA   |
| I <sub>H</sub>      | holding current                   | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>   | -    | 2.2 | 15  | mA   |
| V <sub>T</sub>      | on-state voltage                  | I <sub>T</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>   | -    | 1.4 | 1.7 | V    |
| V <sub>GT</sub>     | gate trigger voltage              | $V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T}_j = 25 \text{ °C};$<br>Fig. 11   | -    | 0.7 | 1   | V    |
|                     |                                   | $V_{D}$ = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C;<br>Fig. 11   | 0.25 | 0.4 | -   | V    |
| I <sub>D</sub>      | off-state current                 | V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C  | -    | 0.1 | 0.5 | mA   |
| Dynamic             | characteristics                   |  |      |     |     | ,    |
| dV <sub>D</sub> /dt | rate of rise of off-state voltage | $V_{DM} = 402 \text{ V}; \text{ T}_{j} = 125 \text{ °C}; (V_{DM} = 67\% \text{ of } V_{DRM});$ exponential waveform; gate open circuit | -    | 50  | -   | V/µs |
| t <sub>gt</sub>     | gate-controlled turn-on time      | $V_{\rm D}$ = 600 V; I <sub>TM</sub> = 6 A; I <sub>G</sub> = 0.1 A;<br>dI <sub>G</sub> /dt = 5 A/µs                                    | -    | 2   | -   | μs   |
| gi                  |                                   |  |      |     |     |      |





# 11. Package outline

| astic | singl      | le-en        | ded p        | acka         | ge; 3      | lead   | s (in- | line)        |                           |              |            |            |           |            | SO         |
|-------|------------|--------------|--------------|--------------|------------|--------|--------|--------------|---------------------------|--------------|------------|------------|-----------|------------|------------|
|       |            |              |              |              |            |        |        |              |                           |              |            |            |           |            |            |
| DIMEN |            | 2 (mm        | are the      | origin       | al dim     | ncione | -)     |              | 0<br>L                    | 2.5<br>scale | 5 mr<br>   | n          |           |            |            |
| UNIT  | A          | b            | C            | D            | E          | e      | •1     | L            | L1 <sup>(1)</sup><br>max. | Р            | Q          | q          | w         |            |            |
| mm    | 2.8<br>2.3 | 0.88<br>0.65 | 0.58<br>0.47 | 11.1<br>10.5 | 7.8<br>7.2 | 2.29   | 4.58   | 16.5<br>15.3 | 2.54                      | 3.1<br>2.5   | 1.5<br>0.9 | 3.9<br>3.5 | 0.254     |            |            |
| Note  |            |              |              |              |            |        |        |              |                           |              |            |            | larities. |            |            |
|       | UTLIN      |              |              |              |            |        |        |              | RENCE                     |              | lermina    | li inegu   | nannes.   | EUROPEAN   |            |
| VE    | ERSIO      | N            |              | IEC          |            |        | JEDEO  |              |                           | EIAJ         |            |            |           | PROJECTION | ISSUE DATE |
| ;     | SOT82      | 2            |              |              |            |        |        |              |                           |              |            |            |           |            | 97-06-11   |
|       |            |              |              |              |            |        |        |              |                           |              |            |            |           |            |            |

## 12. Legal information

#### Data sheet status

| Document status [1][2]               | Product<br>status [3] | Definition  |
|--------------------------------------|-----------------------|---|
| Objective<br>[short] data<br>sheet   | Development           | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification         | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production            | This document contains the product specification.   |

[1] Please consult the most recently issued document before initiating or completing a design.

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